

2N7002PV

60 V, 350 mA N-channel Trench MOSFET

Rev. 1 — 5 August 2010

Product data sheet

1. Product profile

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

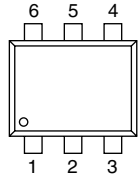
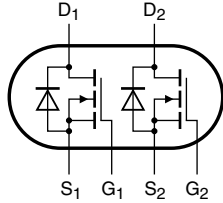
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
V_{DS}	drain-source voltage	$T_{amb} = 25\text{ °C}$	-	-	60	V
V_{GS}	gate-source voltage	$T_{amb} = 25\text{ °C}$	-	-	±20	V
I_D	drain current	$T_{amb} = 25\text{ °C};$ $V_{GS} = 10\text{ V}$	[1]	-	350	mA
$R_{DS(on)}$	drain-source on-state resistance	$T_j = 25\text{ °C};$ $V_{GS} = 10\text{ V};$ $I_D = 500\text{ mA}$	-	1	1.6	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



2. Pinning information

Table 2. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		
2	G1	gate1		
3	D2	drain2		
4	S2	source2		
5	G2	gate2		
6	D1	drain1		

msd901

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
2N7002PV	-	plastic surface-mounted package; 6 leads	SOT666

4. Marking

Table 4. Marking codes

Type number	Marking code
2N7002PV	ZF

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transistor					
V_{DS}	drain-source voltage	$T_{amb} = 25\text{ °C}$	-	60	V
V_{GS}	gate-source voltage	$T_{amb} = 25\text{ °C}$	-	±20	V
I_D	drain current	$V_{GS} = 10\text{ V}$	[1]		
		$T_{amb} = 25\text{ °C}$	-	350	mA
		$T_{amb} = 100\text{ °C}$	-	250	mA
I_{DM}	peak drain current	$T_{amb} = 25\text{ °C}$; single pulse; $t_p \leq 10\text{ }\mu\text{s}$	-	1.2	A

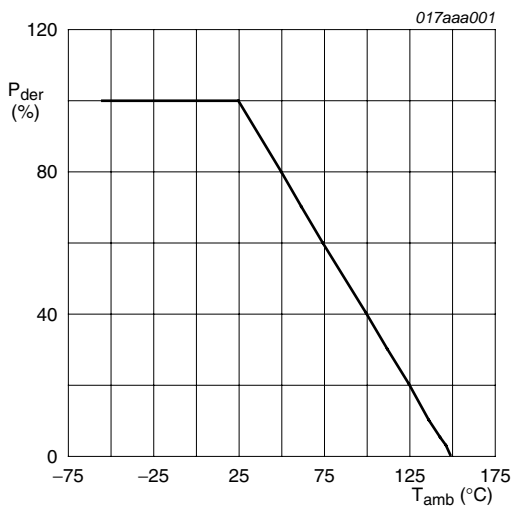
Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	330	mW
			[1]	-	390	mW
		T _{sp} = 25 °C	-	1090	mW	
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	350	mA
Per device						
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	500	mW
T _j	junction temperature				150	°C
T _{amb}	ambient temperature		-55	+150		°C
T _{stg}	storage temperature		-65	+150		°C

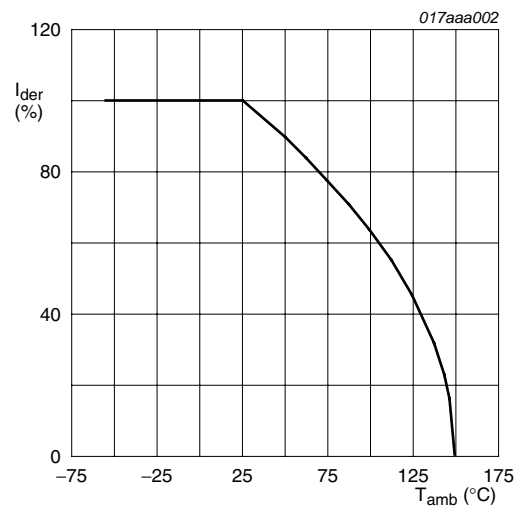
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



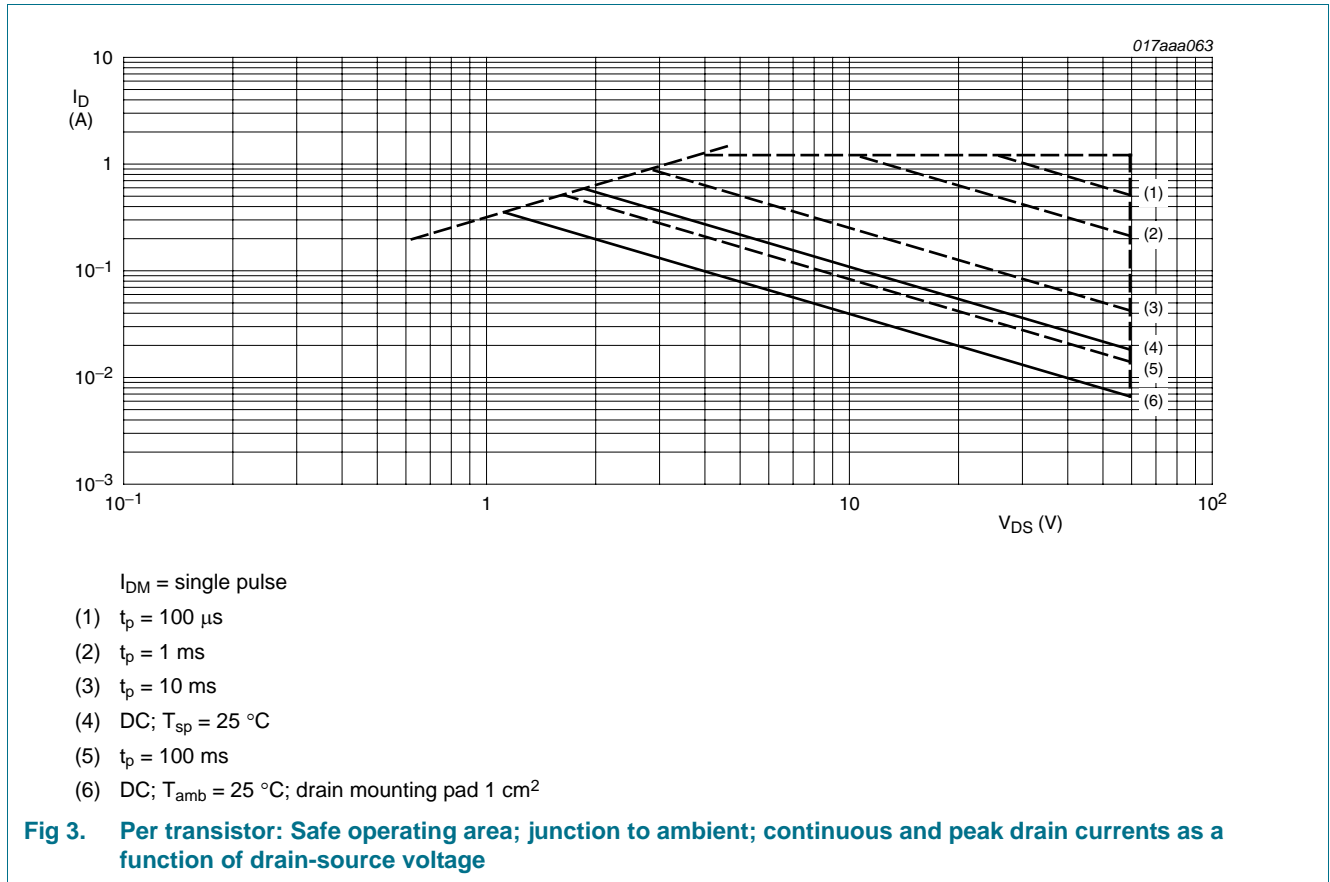
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature



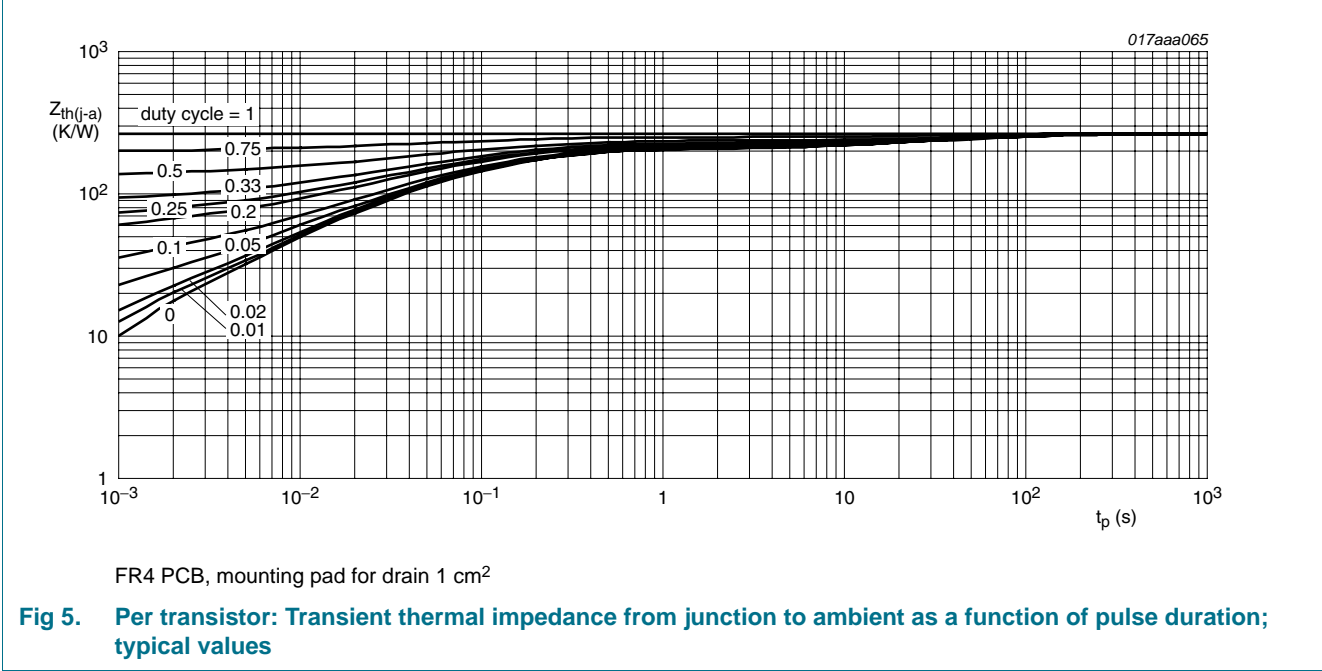
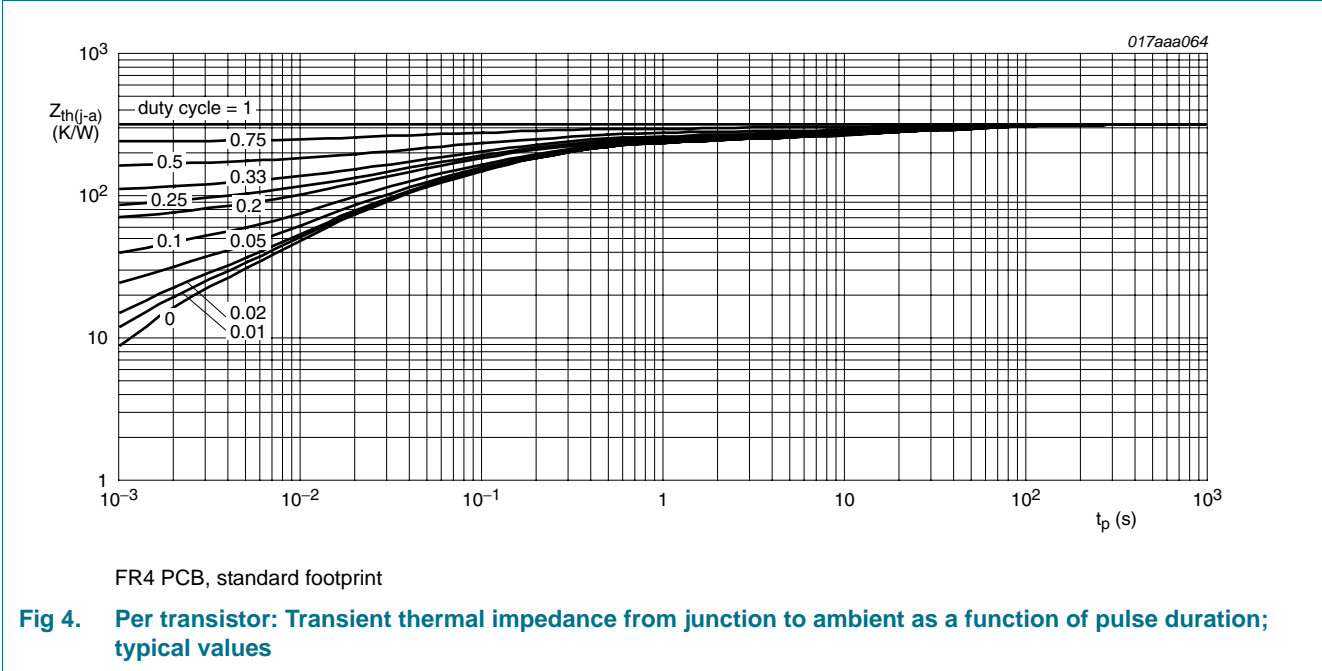
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	330	380 K/W
			[2]	-	280	320 K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	115	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	250 K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .



7. Characteristics

Table 7. Characteristics
 $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10\text{ }\mu\text{A}; V_{GS} = 0\text{ V}$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250\text{ }\mu\text{A}; V_{DS} = V_{GS}$	1.1	1.75	2.4	V
I_{DSS}	drain leakage current	$V_{DS} = 60\text{ V}; V_{GS} = 0\text{ V}$	$T_j = 25\text{ }^\circ\text{C}$			
			-	-	1	μA
			-	-	10	μA
I_{GSS}	gate leakage current	$V_{GS} = \pm 20\text{ V}; V_{DS} = 0\text{ V}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance		[1]			
		$V_{GS} = 5\text{ V}; I_D = 50\text{ mA}$	-	1.3	2	Ω
		$V_{GS} = 10\text{ V}; I_D = 500\text{ mA}$	-	1	1.6	Ω
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 200\text{ mA}$	[1]	-	400	mS
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 300\text{ mA};$	-	0.6	0.8	nC
Q_{GS}	gate-source charge	$V_{DS} = 30\text{ V};$	-	0.2	-	nC
Q_{GD}	gate-drain charge	$V_{GS} = 4.5\text{ V}$	-	0.2	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 10\text{ V};$	-	30	50	pF
C_{oss}	output capacitance	$f = 1\text{ MHz}$	-	7	-	pF
C_{rss}	reverse transfer capacitance		-	4	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DD} = 50\text{ V};$	-	3	6	ns
t_r	rise time	$R_L = 250\text{ }\Omega;$	-	4	-	ns
$t_{d(off)}$	turn-off delay time	$V_{GS} = 10\text{ V};$	-	10	20	ns
t_f	fall time	$R_G = 6\text{ }\Omega$	-	5	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 115\text{ mA}; V_{GS} = 0\text{ V}$	0.47	0.75	1.1	V

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.01$.

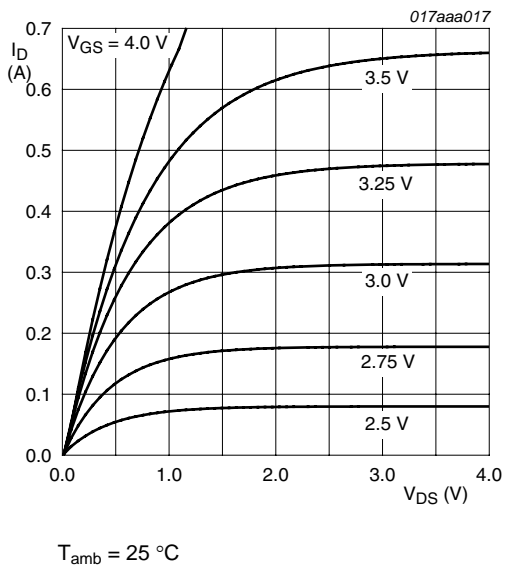


Fig 6. Per transistor: Output characteristics: drain current as a function of drain-source voltage; typical values

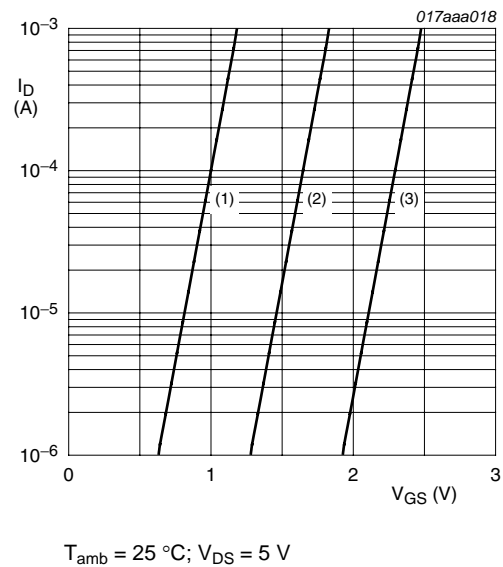


Fig 7. Per transistor: Sub-threshold drain current as a function of gate-source voltage

$T_{amb} = 25\text{ °C}; V_{DS} = 5\text{ V}$

- (1) minimum values
- (2) typical values
- (3) maximum values

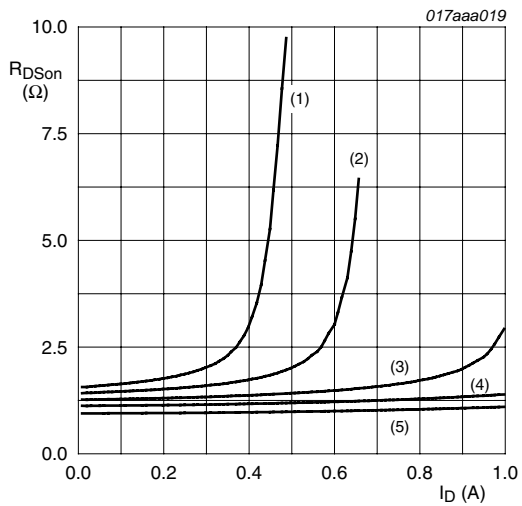


Fig 8. Per transistor: Drain-source on-state resistance as a function of drain current; typical values

- $T_{amb} = 25\text{ °C}$
- (1) $V_{GS} = 3.25\text{ V}$
 - (2) $V_{GS} = 3.5\text{ V}$
 - (3) $V_{GS} = 4\text{ V}$
 - (4) $V_{GS} = 5\text{ V}$
 - (5) $V_{GS} = 10\text{ V}$

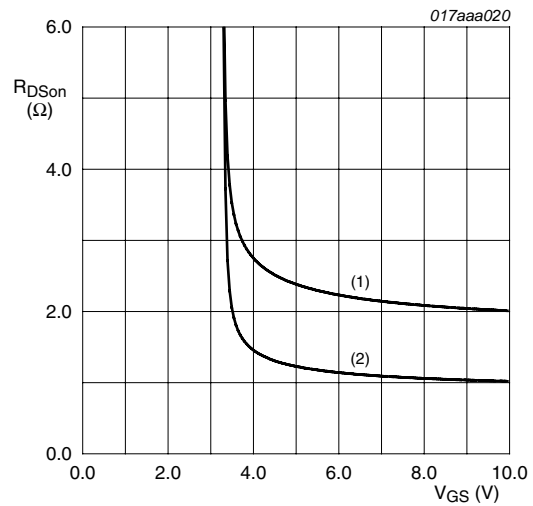
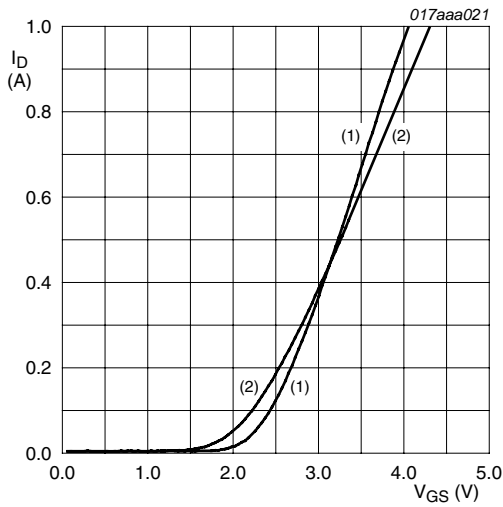


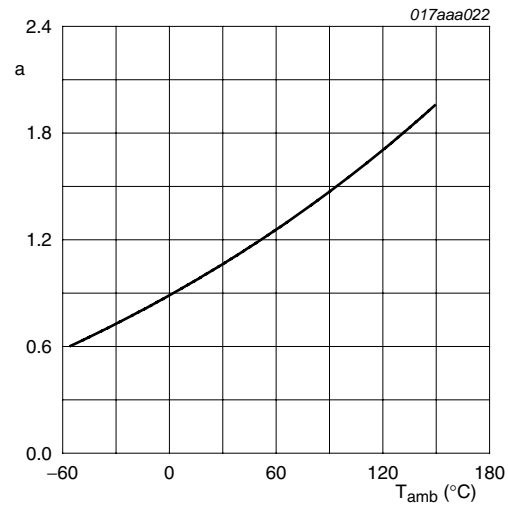
Fig 9. Per transistor: Drain-source on-state resistance as a function of gate-source voltage; typical values

- $I_D = 500\text{ mA}$
- (1) $T_{amb} = 150\text{ °C}$
 - (2) $T_{amb} = 25\text{ °C}$



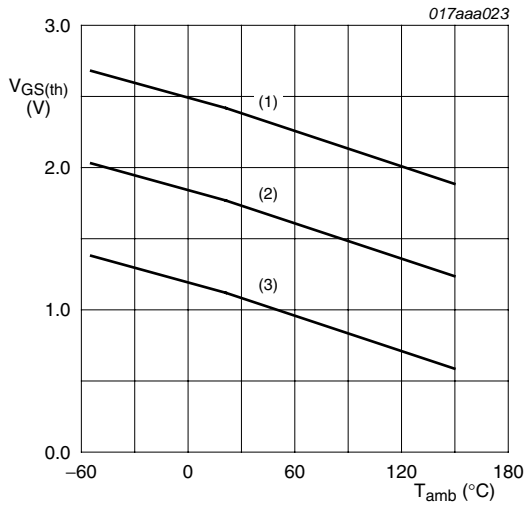
$V_{DS} > I_D \times R_{DS(on)}$
 (1) $T_{amb} = 25\text{ }^\circ\text{C}$
 (2) $T_{amb} = 150\text{ }^\circ\text{C}$

Fig 10. Per transistor: Transfer characteristics: drain current as a function of gate-source voltage; typical values



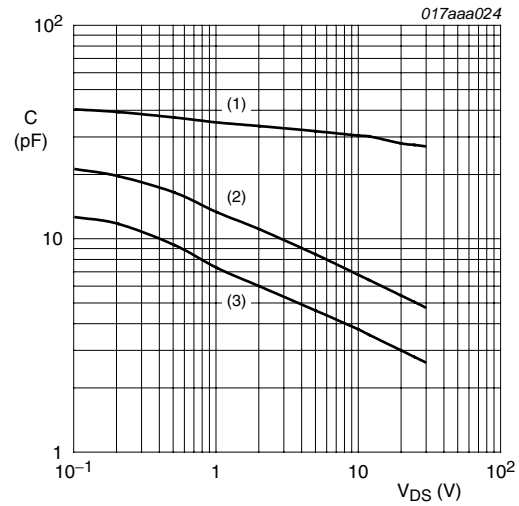
$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^\circ\text{C})}}$$

Fig 11. Per transistor: Normalized drain-source on-state resistance as a function of ambient temperature; typical values



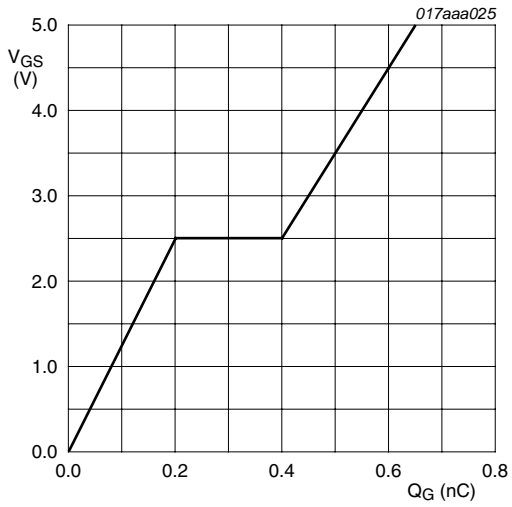
$I_D = 0.25\text{ mA}; V_{DS} = V_{GS}$
 (1) maximum values
 (2) typical values
 (3) minimum values

Fig 12. Per transistor: Gate-source threshold voltage as a function of ambient temperature



$f = 1\text{ MHz}; V_{GS} = 0\text{ V}$
 (1) C_{iss}
 (2) C_{oss}
 (3) C_{rss}

Fig 13. Per transistor: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 300 \text{ mA}$; $V_{DS} = 30 \text{ V}$; $T_{amb} = 25 \text{ }^\circ\text{C}$

Fig 14. Per transistor: Gate-source voltage as a function of gate charge; typical values

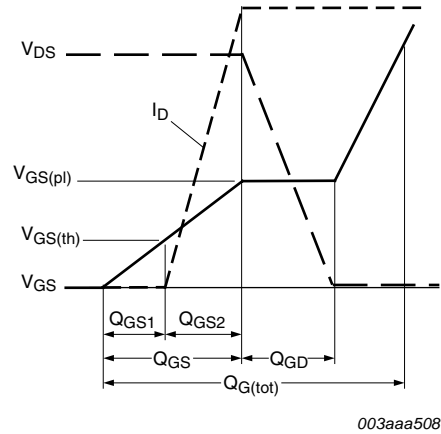
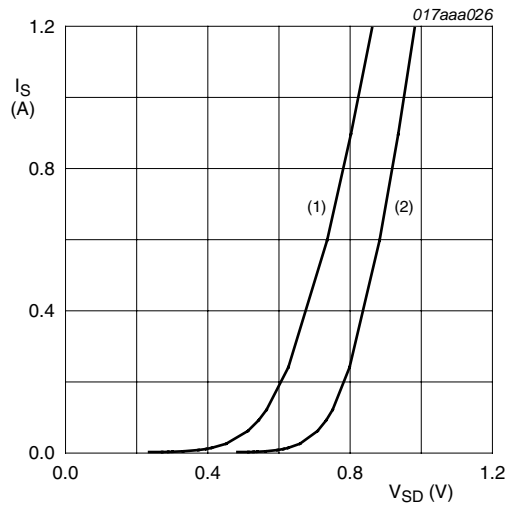


Fig 15. Per transistor: Gate charge waveform definitions

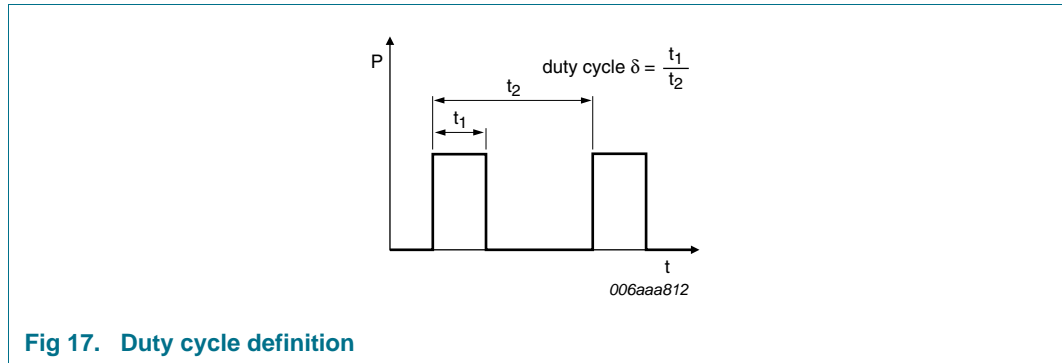


$V_{GS} = 0 \text{ V}$

- (1) $T_{amb} = 150 \text{ }^\circ\text{C}$
- (2) $T_{amb} = 25 \text{ }^\circ\text{C}$

Fig 16. Per transistor: Source current as a function of source-drain voltage; typical values

8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

Plastic surface-mounted package; 6 leads

SOT666

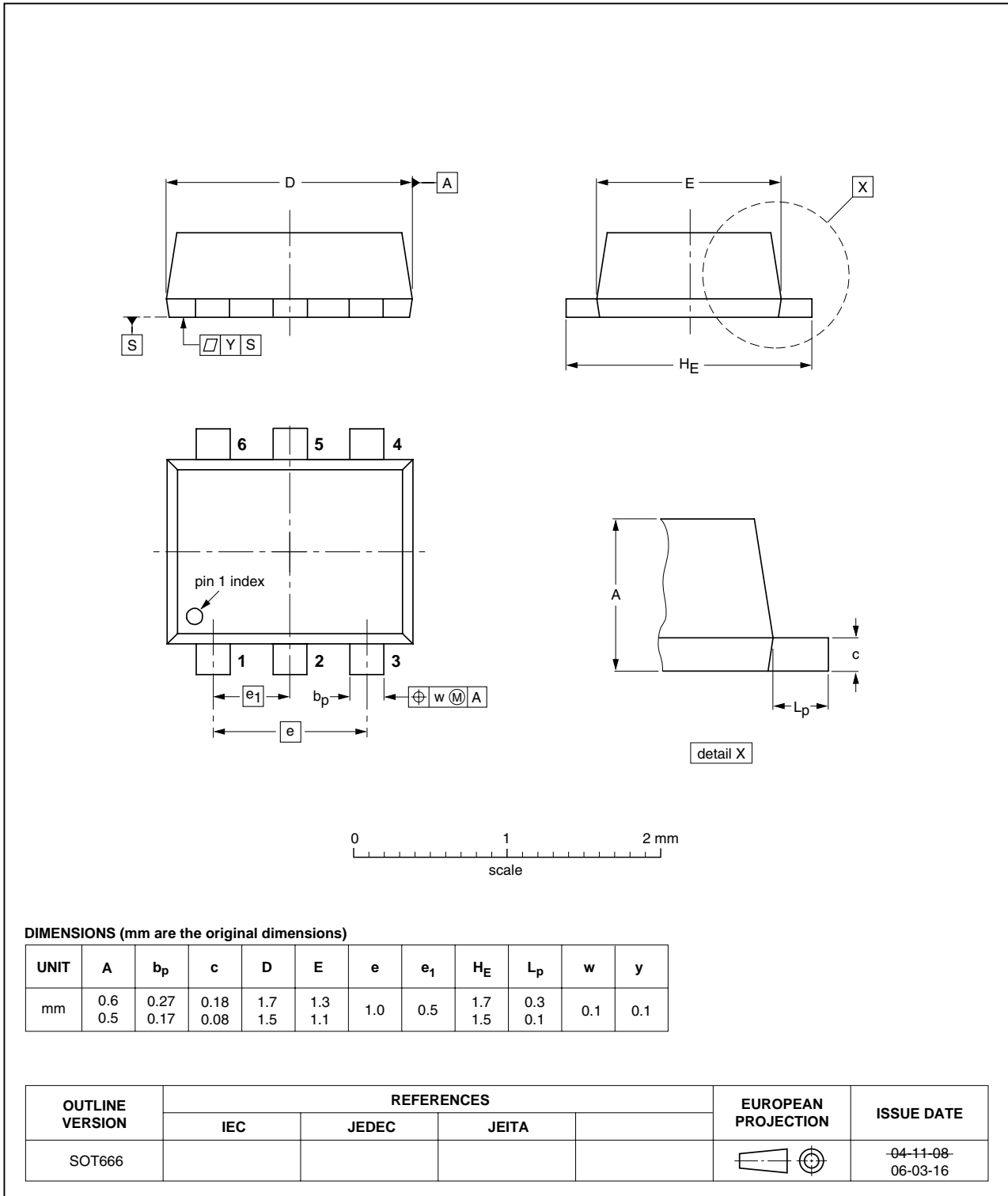
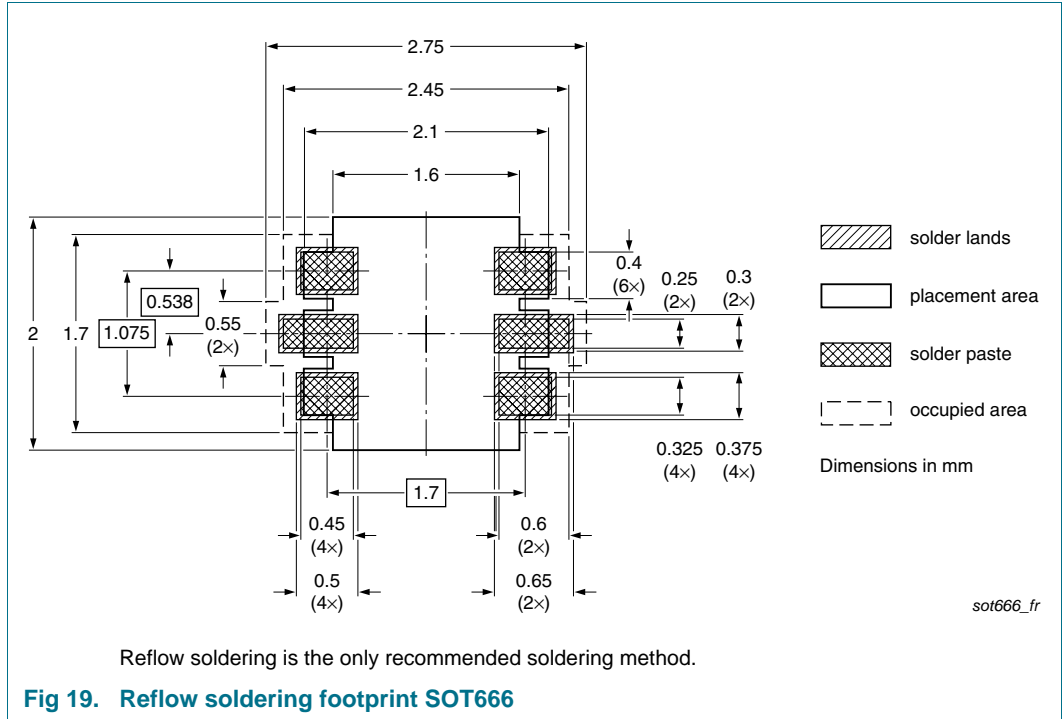


Fig 18. Package outline SOT666

10. Soldering



11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2N7002PV v.1	20100805	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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